Silicon PNP transistor in a TO-92 Plastic Package.

High P

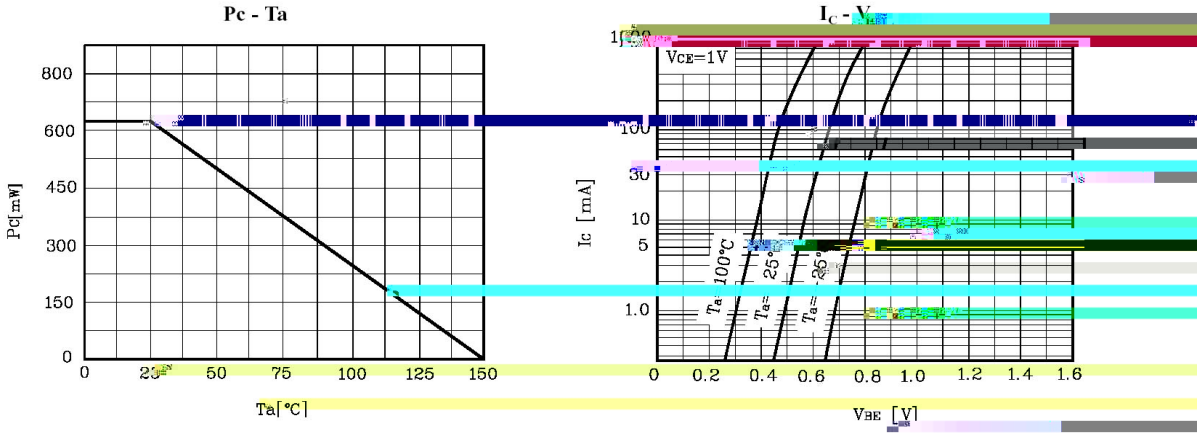
/ Absolute Maximum Ratings(Ta=25)

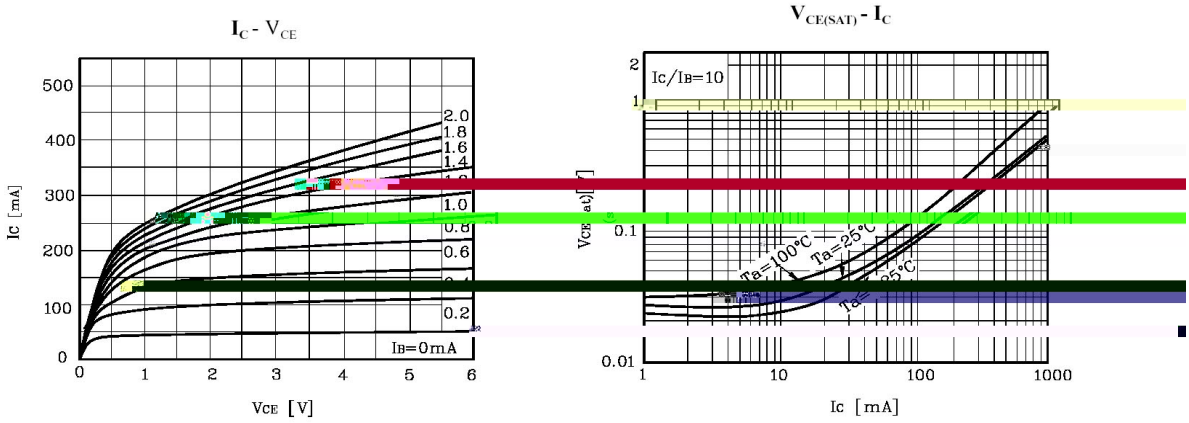
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Base Current - Continuous	I_B	-100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

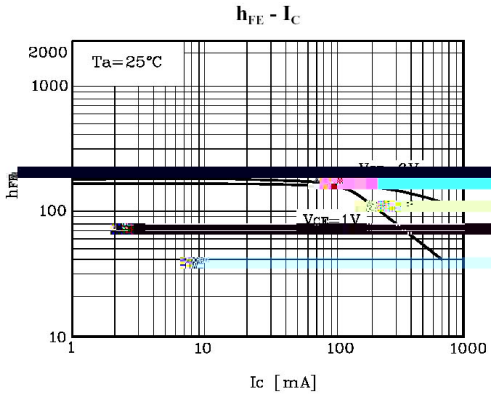
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-25V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-3.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1.0V I_C=-50mA	64		276	
	$h_{FE(2)}$	V_{CE}=-1.0V I_C=-500mA	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA I_B=-50mA		-0.18	-0.6	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-500mA I_B=-50mA		-0.95	-1.2	V
Base to Emitter Voltage	V_{BE}	V_{CE}=-1.0V I_C=-10mA		-0.67	-0.7	V

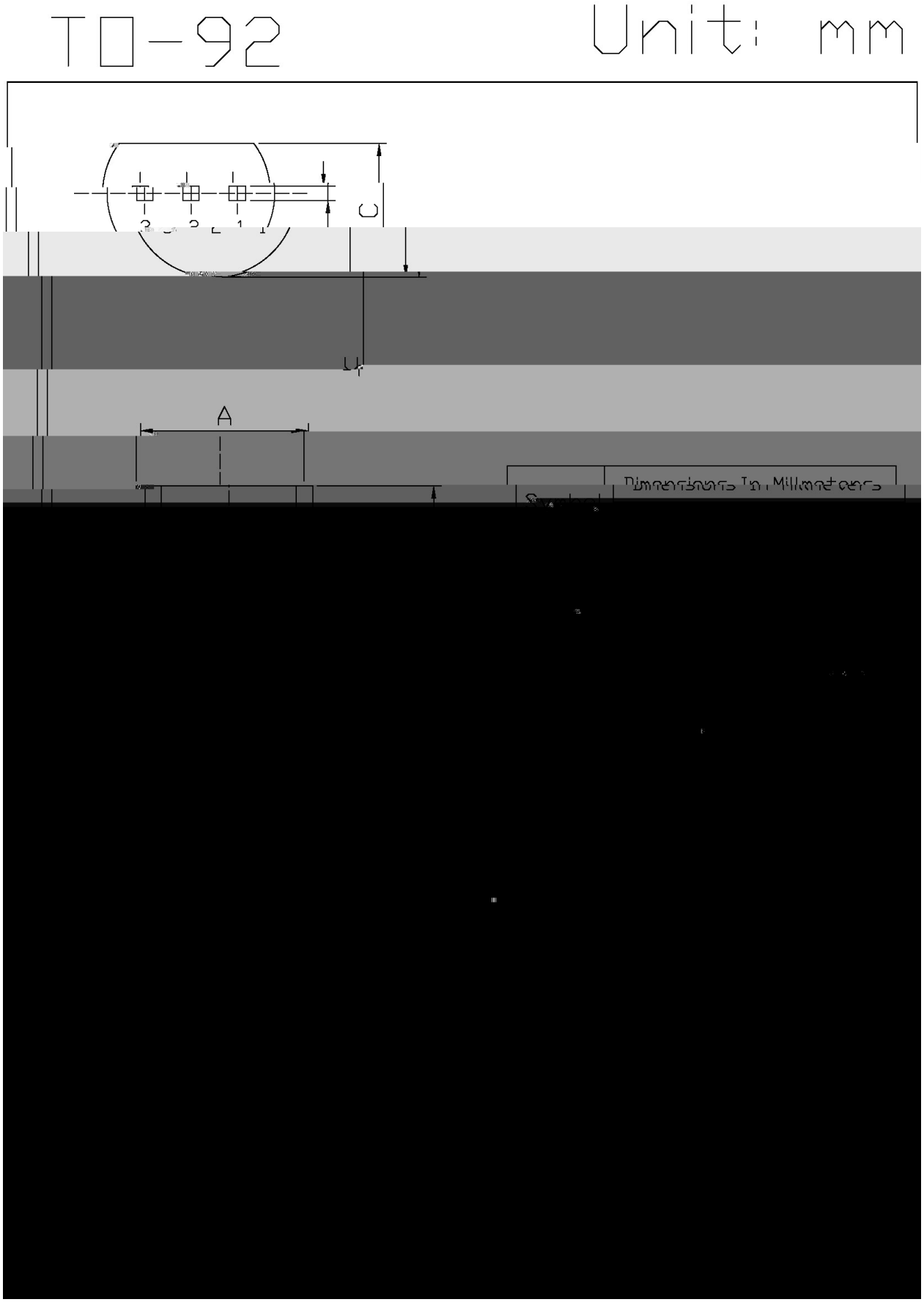
/ Electrical Characteristic Curve



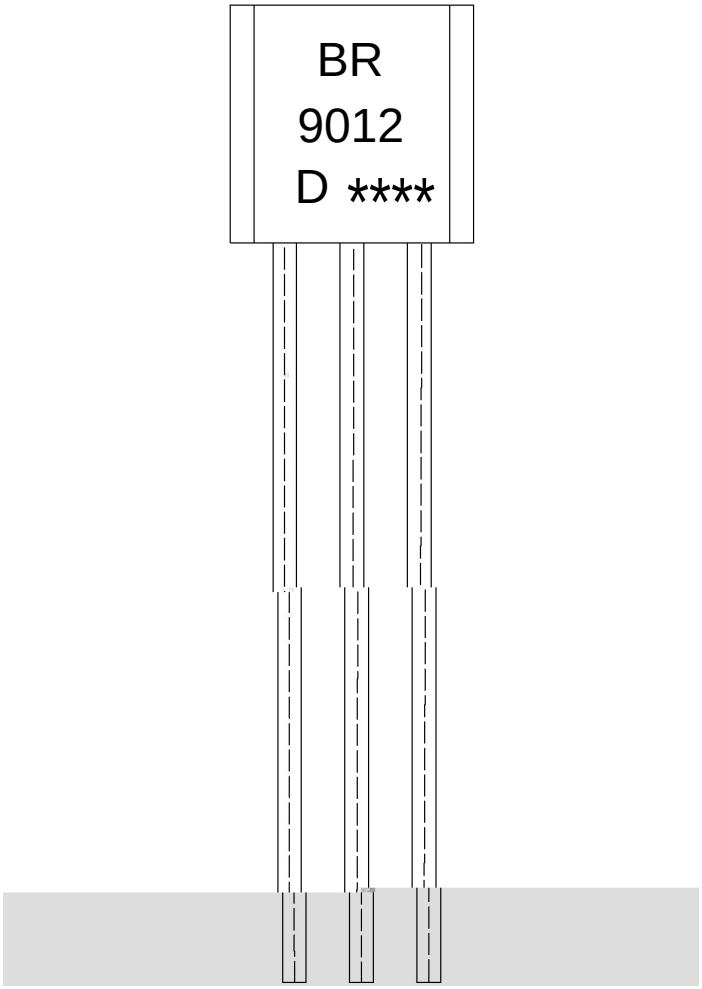




/ Package Dimensions



/ Marking Instructions



Note:

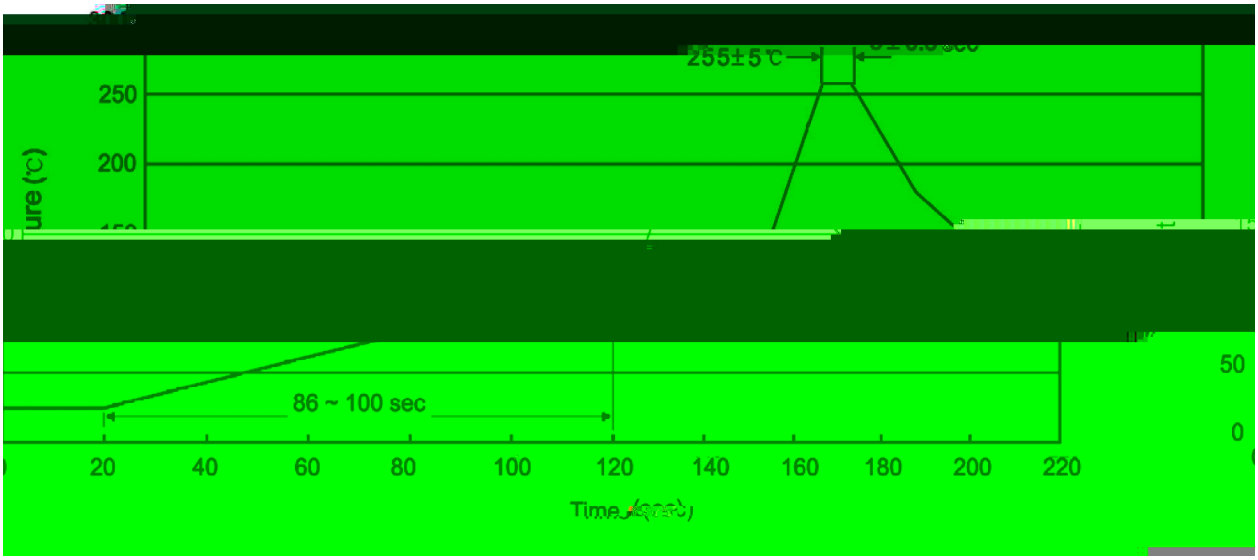
BR: Company Code.

9012: Product Type.

D: h_{FE} Classifications Symbol.

****: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270 5	10 1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK